

Numerical Modelling of Transport Processes in Semiconductors

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Abstract

The peculiarities of electric current in semiconductors with nonuniform distribution of charge carriers are studied. The semiclassical drift-diffusion equations consisting of the continuity equations and the Poisson equation are solved numerically using Rusanov finite-difference scheme of third order. The different types of boundary conditions are numerically investigated. It is shown that the stability of the Rusanov scheme for the problem considered is achieved with the Neumann type boundary conditions. These conditions correspond to the absence of diffusion through semiconductor surface. Special set of parameters is found under which a very interesting and unusual transient effect of negative current in nonuniform semiconductors appears. Different regimes of negative current are considered for realistic semiconductor materials.

PACS: 02.60.Cb

Keywords: Numerical simulation, semiconductors

The study of electric current in semiconductors is important for describing and modelling semiconductor devices. The action of external radiation can result in the formation of a nonuniform distribution of charge carriers in a semiconductor sample. The transport processes in semiconductors with essentially nonuniform distribution of carriers can be quite specific. For instance, in a semiconductor sample biased with an external constant voltage the electric current may turn against the applied voltage [1,2]. Of course, it can happen only as a short time fluctuation after which the current turns back becoming positive. So we can talk about this only as about a transient effect. This unusual transient effect of negative current is interesting by itself although there might be some useful applications suggested. For example, it can be used for measuring physical characteristics of semiconductor materials or for constructing electronic controlling devices [3].

Transport properties of semiconductors are usually described by the semiclassical drift-diffusion equations [4]. In dimensionless units we have the continuity equation

$$\frac{\partial \rho_i}{\partial t} + \mu_i \frac{\partial}{\partial x} (\rho_i E) - D_i \frac{\partial^2 \rho_i}{\partial x^2} + \gamma_i \rho_i = 0 , \quad (1)$$

where $0 \leq x \leq 1$, $t > 0$, $i = 1, 2$, and the Poisson equation

$$\frac{\partial E}{\partial x} = 4\pi(\rho_1 + \rho_2) . \quad (2)$$

Here, $\rho_1 = \rho_1(x, t)$ and $\rho_2 = \rho_2(x, t)$ are charge densities; $E = E(x, t)$, electric field. The functions ρ_1 , ρ_2 , E are unknown functions to be found from equations (1) and (2).

The considered semiconductor sample of length L is characterized by the following parameters: μ_i , mobilities; D_i , diffusion coefficients; γ_i , relaxation widths. Two types, ($i = 1, 2$), of charge carriers are assumed: positive and negative, so that $\rho_1 > 0$, $\mu_1 > 0$, and $\rho_2 < 0$, $\mu_2 < 0$. We consider the semiconductor sample of the length $L = 1$.

Initial distribution of charge carriers is modelled by the Gaussian form, which e.g. corresponds to the distribution of charges in a semiconductor irradiated by an ion beam. For $t = 0$,

$$\rho_i(x, 0) \equiv \frac{Q_i}{Z_i} \exp \left\{ -\frac{(x - a_i)^2}{2b_i} \right\} , \quad (0 < a_i < 1) , \quad (3)$$

where $Q_i = \int_0^1 \rho_i(x, 0) dx$ and $Z_i = \int_0^1 \exp \left\{ -\frac{(x - a_i)^2}{2b_i} \right\} dx$. Note that the initial distribution for the electric field $E(x, 0)$ is to be found from equations (1) and (2), using (3) and given boundary conditions.

There are two possibilities of posing boundary conditions for functions $\rho_i(x, t)$. The Dirichlet type,

$$\rho_i(0, t) = \rho_i(1, t) = 0, \quad (i = 1, 2),$$

which corresponds to the absence of the drift current ($j_i \equiv \mu_i \rho_i E = 0$) at the semiconductor surface, and the Neumann type,

$$\left. \frac{\partial \rho_i}{\partial t} \right|_{x=0} = \left. \frac{\partial \rho_i}{\partial t} \right|_{x=1} = 0, \quad (i = 1, 2),$$

which corresponds to the absence of diffusion through the semiconductor surface.

We considered both types of boundary conditions for ρ_i . It turned out that calculational procedure is less stable in the case of the Dirichlet boundary conditions because of the accumulation of charges at the semiconductor surfaces. As a result, discontinuities appear in the vicinity of the boundaries $x = 0$ and $x = 1$, which leads to numerical instability. In practice, it is also more difficult to arrange that the drift current through a semiconductor surface be absent. In what follows, we use the Neumann type of boundary conditions for the system (1) and (2).

The role of boundary conditions for the electric field $E(x, t)$ is played by the voltage integral

$$\int_0^1 E(x, t) dx = 1.$$

Our aim is to study the peculiarity in the behaviour of the electric current through the semiconductor sample

$$J(t) = \int_0^1 j_{tot}(x, t) dx, \quad (4)$$

where

$$j_{tot}(x, t) = \left(\mu_1 E - D_1 \frac{\partial}{\partial x} \right) \rho_1 + \left(\mu_2 E - D_2 \frac{\partial}{\partial x} \right) \rho_2 + \frac{1}{4\pi} \frac{\partial E}{\partial t}. \quad (5)$$

We also are interested in the electric currents at the left ($x = 0$) and right ($x = 1$) surfaces of the semiconductor, $J_0(t) \equiv j_{tot}(0, t)$ and $J_1(t) \equiv j_{tot}(1, t)$. Let us note that $J(t)$ can be presented in the integral form

$$\begin{aligned} J(t) = & \int_0^1 [\mu_1 \rho_1(x, t) + \mu_2 \rho_2(x, t)] E(x, t) dx + \\ & + D_1 [\rho_1(0, t) - \rho_1(1, t)] + D_2 [\rho_2(0, t) - \rho_2(1, t)], \end{aligned}$$

which is more convenient for numerical computation.

Numerical investigation showed that the known explicit finite difference schemes of the second order are strongly unstable for the system (1) and (2). Because of this, we resorted to the third-order accuracy finite-difference scheme suggested by Rusanov [5] which proved to be very efficient for discontinuous solutions. The calculational procedure for the Rusanov scheme is constructed as follows. We consider the vector-function $u_m^{(n)} = \{\rho_1(x_m, t_n), \rho_2(x_m, t_n), E_m(x_m, t_n)\}$, where $x_m = mh$ and $t_n = n\tau$, $m = 0, 1, \dots, M$; $n = 0, 1, \dots$. The grid space step is $h = 1/M$. The time step τ is chosen so that the calculational procedure be stable. The parameter σ in the Rusanov scheme, responsible for the stability of calculations, is $\sigma = 0.45$ for $\tau/h = 0.125$. We will not present the computational scheme explicitly since it is quite cumbersome. Let us better dwell upon the approximation of boundary conditions for $\rho_i(x, t)$ ($i = 1, 2$) and for $E(x, t)$. Numerical modelling showed that the Neumann type of boundary conditions for the charge carriers are to be approximated with the third order accuracy for the time layers $t = t_n = n\tau$ and auxiliary time layers $t = t_n^{(2)} = t_n + 2\tau/3$ at the integer boundary nodes:

$$\rho_i(x_M, t) = \frac{1}{3} [4\rho_i(x_{M-1}, t) - \rho_i(x_{M-2}, t)] , \quad \rho_i(x_0, t) = \frac{1}{3} [4\rho_i(x_1, t) - \rho_i(x_2, t)] ,$$

and with the second order accuracy for the half-integer boundary nodes at the auxiliary time layer $t = t_n^{(1)} = n\tau + \tau/3$:

$$\rho_i(x_{M+1/2}, t) = \rho_i(x_{M-1/2}, t) , \quad \rho_i(x_{-1/2}, t) = \rho_i(x_{1/2}, t) ,$$

where $x_{m+1/2} = mh + 1/2$, $m = 0, 1, \dots, M$, $n = 1, 2, \dots$.

To approximate the boundary conditions for the electric field $E(x, t)$, given in the integral form, it was necessary to rewrite it in the form convenient for calculations:

$$E(x, t) = 1 + 4\pi \left[Q(x, t) - \int_0^1 Q(x, t) dx \right] , \quad Q(x, t) = \int_0^x [\rho_1(y, t) + \rho_2(y, t)] dy .$$

Then $E(0, t)$ and $E(1, t)$ are given by the above formulas for $x = 0$ and $x = 1$. At each time layer $t_n = n\tau$, we checked whether the equality $\int_0^1 E(x, t) dx = 1$ holds true.

We have accomplished numerical calculations for different sets of parameters a_i , b_i , μ_i , D_i , γ_i , and Q_i . It turned out that for some values of parameters there exists an unusual transient effect when the electric current turns against the applied voltage. This effect of *negative current* occurs on the whole manifold of parameters. Here we illustrate it for the case of a unipolar semiconductor, when $Q_1 \equiv Q > 0$ and $Q_2 = 0$. Other parameters are set as $\mu_1 = 1$, $\mu_2 = 0$, $D_i \ll 1$, $\gamma_i \ll 1$, and the notation $a_1 \equiv a$, $b_1 \equiv b$ is used.

Fig. 1 shows the total electric current (4) through the semiconductor sample, as a function of time, for the injected electric charge $Q = 0.5$, the initial Gaussian distribution width $b = 0.1$, and for different locations of the peak of this charge distribution, a . As is seen, the negative electric current happens at the initial stage of the process for $a < 0.5$, such as $a = 0.1$ and $a = 0.25$, but does not exist for $a \geq 0.5$.

Fig. 2 presents the total electric current versus time for $Q = 3$ and $b = 0.5$, with varying locations a . Again, the negative current appears for $a < 0.5$ but does not occur for $a > 0.5$. More accurately, the conditions on a and Q , sufficient for the occurrence of the negative current, are

$$a < \frac{1}{2} - \frac{1}{4\pi Q}, \quad Q > \frac{1}{2\pi}.$$

The existence of the transient effect of negative electric current is the most interesting result of the numerical modelling we have accomplished for semiconductors.

References

- [1] V.I. Yukalov and E.P. Yukalova, Phys. Lett. A 236 (1997) 113.
- [2] V.I. Yukalov, E.P. Yukalova, and M.R. Singh, Phys. Rev. B 59 (1999) 10111.
- [3] V.I. Yukalov and E.P. Yukalova, Phys. Status Solidi A 77 (1999) 267.
- [4] C.M. Snowden, Introduction to Semiconductor Device Modelling (World Scientific, Singapore, 1986).
- [5] V.V. Rusanov, J. Comput. Phys. 5 (1970) 807.

Figure captions

Fig. 1. Total electric current as a function of time for $Q = 0.5$, $b = 0.1$ and different locations for the peak of the initial charge-carriers distribution: $a = 0.1$ (1 curve, solid line); $a = 0.25$ (2 curve, long-dashed line); $a = 0.5$ (3 curve, short-dashed line); and $a = 0.75$ (4 curve, dotted line).

Fig. 2. Electric current through the semiconductor sample versus time for $Q = 3$, $b = 0.5$, and varying initial charge locations a , which take the same sequence of values as in Fig. 1.